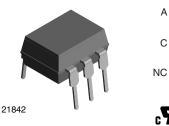
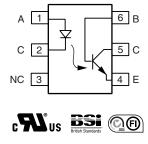


ROHS COMPLIANT

Vishay Semiconductors

Optocoupler, Phototransistor Output, with Base Connection





DESCRIPTION

Each optocoupler consists of gallium arsenide infrared LED and a silicon NPN phototransistor.

i179004-5

AGENCY APPROVALS

- Underwriters laboratory file no. E52744
- BSI: EN 60065:2002, EN 60950:2000
- FIMKO; EN 60065, EN 60335, EN 60950 certificate no. 25156

FEATURES

- Isolation test voltage 5000 V_{RMS}
- Interfaces with common logic families
- Input-output coupling capacitance < 0.5 pF
- Industry standard dual-in-line 6 pin package
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC

APPLICATIONS

- AC mains detection
- · Reed relay driving
- Switch mode power supply feedback
- Telephone ring detection
- Logic ground isolation
- Logic coupling with high frequency noise rejection

ORDER INFORMATION				
PART	REMARKS			
4N35	CTR > 100 %, DIP-6			
4N36	CTR > 100 %, DIP-6			
4N37	CTR > 100 %, DIP-6			

ABSOLUTE MAXIMUM RATINGS ⁽¹⁾							
PARAMETER	TEST CONDITION SYMBOL		VALUE	UNIT			
INPUT							
Reverse voltage		V _R	6	V			
Forward current		I _F	50	mA			
Surge current	t ≤ 10 µs	I _{FSM}	1	А			
Power dissipation		P _{diss}	70	mW			
OUTPUT							
Collector emitter breakdown voltage		V _{CEO}	70	V			
Emitter base breakdown voltage		V _{EBO}	7	V			
Collector current		Ι _C	50	mA			
	$t \le 1 ms$	Ι _C	100	mA			
Power dissipation		P _{diss}	70	mW			
COUPLER							
Isolation test voltage		V _{ISO}	5000	V _{RMS}			
Creepage			≥ 7	mm			
Clearance			≥7	mm			
Isolation thickness between emitter and detector			≥ 0.4	mm			

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ABSOLUTE MAXIMUM RATINGS ⁽¹⁾								
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT				
COUPLER								
Comparative tracking index	DIN IEC 112/VDE 0303, part 1		175					
Isolation resistance	$V_{IO} = 500 \text{ V}, \text{ T}_{amb} = 25 ^{\circ}\text{C}$	R _{IO}	10 ¹²	Ω				
	$V_{IO} = 500 \text{ V}, \text{ T}_{amb} = 100 ^{\circ}\text{C}$	R _{IO}	10 ¹¹	Ω				
Storage temperature		T _{stg}	- 55 to + 150	°C				
Operating temperature		T _{amb}	- 55 to + 100	°C				
Junction temperature		Tj	100	°C				
Soldering temperature ⁽²⁾	max.10 s dip soldering: distance to seating plane ≥ 1.5 mm	T _{sld}	260	°C				

Notes

⁽¹⁾ $T_{amb} = 25 \text{ °C}$, unless otherwise specified.

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.

⁽²⁾ Refer to wave profile for soldering condditions for through hole devices (DIP).

PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
INPUT			<u> </u>		I	I	
Junction capacitance	V _R = 0 V, f = 1 MHz		Cj		50		pF
Ferrierd	l _F = 10 mA		V _F		1.3	1.5	V
Forward voltage ⁽²⁾	I _F = 10 mA, T _{amb} = - 55 °C		V _F	0.9	1.3	1.7	V
Reverse current ⁽²⁾	V _R = 6 V		I _R		0.1	10	μA
Capacitance	V _R = 0 V, f = 1 MHz		Co		25		pF
OUTPUT							
		4N35	BV _{CEO}	30			V
Collector emitter breakdown voltage ⁽²⁾	I _C = 1 mA	4N36	BV _{CEO}	30			V
vollage		4N37	BV _{CEO}	30			V
Emitter collector breakdown voltage ⁽²⁾	I _E = 100 μA		BV _{ECO}	7			V
OUTPUT							•
	I _C = 100 μA, I _B = 1 μA	4N35	BV _{CBO}	70			V
Collector base breakdown voltage ⁽²⁾		4N36	BV _{CBO}	70			V
Voltage		4N37	BV _{CBO}	70			V
	$V_{CE} = 10 \text{ V}, \text{ I}_{F} = 0$	4N35	I _{CEO}		5	50	nA
		4N36	I _{CEO}		5	50	nA
Collector emitter leakage current ⁽²⁾	$V_{CE} = 10 \text{ V}, \text{ I}_{F} = 0$	4N37	I _{CEO}		5	50	nA
	$\label{eq:VcE} \begin{array}{l} V_{CE}=30 \text{ V}, \text{ I}_{F}=0, \\ T_{amb}=100 ^{\circ}\text{C} \end{array}$	4N35	I _{CEO}			500	μA
		4N36	I _{CEO}			500	μA
		4N37	I _{CEO}			500	μA
Collector emitter capacitance	$V_{CE} = 0$		C _{CE}		6		pF
COUPLER							
Resistance, input output ⁽²⁾	V _{IO} = 500 V		R _{IO}	10 ¹¹			Ω
Capacitance, input output	f = 1 MHz		CIO		0.6		pF

Notes

⁽¹⁾ $T_{amb} = 25$ °C, unless otherwise specified.

Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements.

⁽²⁾ Indicates JEDEC registered value.



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CURRENT TRANSFER RATIO							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN	TYP.	MAX	UNIT
DC current transfer ratio ⁽¹⁾	V _{CE} = 10 V, I _F = 10 mA	4N35	CTR _{DC}	100			%
		4N36	CTR _{DC}	100			%
		4N37	CTR _{DC}	100			%
	$V_{CE} = 10 \text{ V}, I_F = 10 \text{ mA}, T_A = -55 \text{ °C to } + 100 \text{ °C}$	4N35	CTR _{DC}	40	50		%
		4N36	CTR _{DC}	40	50		%
		4N37	CTR _{DC}	40	50		%

Note

⁽¹⁾ Indicates JEDEC registered values.

SWITCHING CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Switching time ⁽¹⁾	V_{CC} = 10 V, I_{C} = 2 mA, R_{L} = 100 Ω	t _{on} , t _{off}		10		μs

Note

⁽¹⁾ Indicates JEDEC registered values.

TYPICAL CHARACTERISTICS

 $T_{amb} = 25$ °C, unless otherwise specied

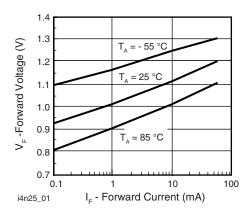


Fig. 1 - Forward Voltage vs. Forward Current

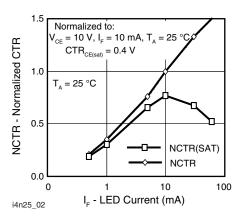


Fig. 2 - Normalized Non-Saturated and Saturated CTR vs. LED Current

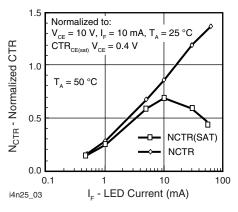


Fig. 3 - Normalized Non-Saturated and Saturated CTR vs. LED Current

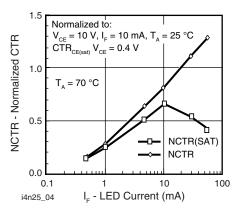


Fig. 4 - Normalized Non-Saturated and Saturated CTR vs. LED Current

4N35, 4N36, 4N37

Vishay Semiconductors Optocoupler, Phototransistor Output, with Base Connection



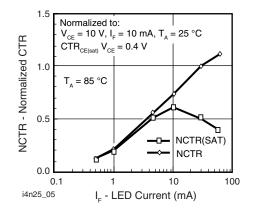


Fig. 5 - Normalized Non-Saturated and Saturated CTR vs. LED Current

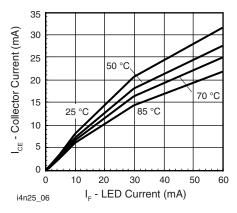


Fig. 6 - Collector Emitter Current vs. Temperature and LED Current

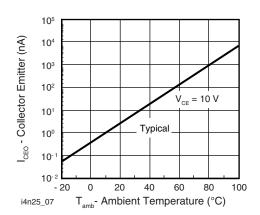


Fig. 7 - Collector Emitter Leakage Current vs. Temperature

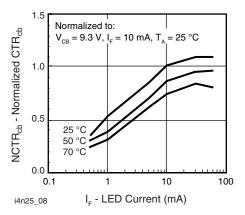


Fig. 8 - Normalized CTR_{cb} vs. LED Current and Temperature

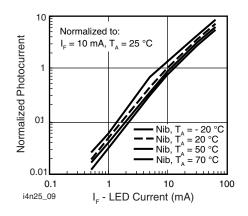


Fig. 9 - Normalized Photocurrent vs. I_F and Temperature

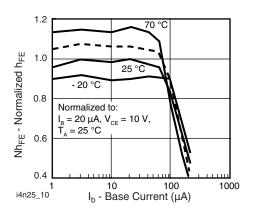


Fig. 10 - Normalized Non-Saturated h_{FE} vs. Base Current and Temperature



Optocoupler, Phototransistor Output, Vishay Semiconductors with Base Connection

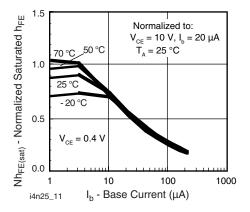


Fig. 11 - Normalized h_{FE} vs. Base Current and Temperature

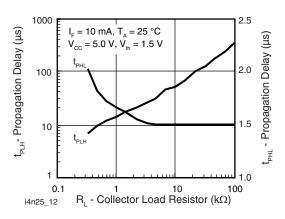


Fig. 12 - Propagation Delay vs. Collector Load Resistor

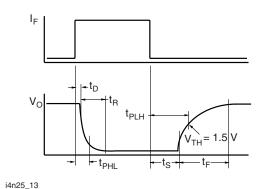
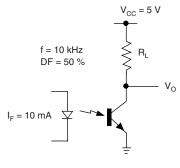


Fig. 13 - Switching Timing

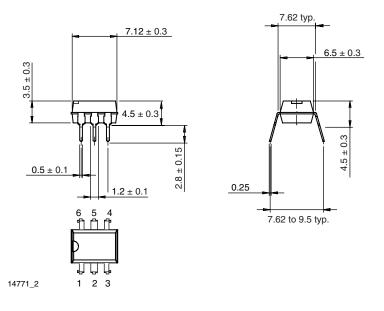


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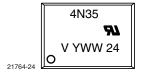
Fig. 14 - Switching Schematic

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PACKAGE DIMENSIONS in millimeters



PACKAGE MARKING







Vishay

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